



2", 3", 4" and 6" wafers

High-quality epitaxial services

Features

- Customer-specific epitaxy on 2", 3", 4" and 6" GaAs substrates
- Layer structures in the Al-In-Ga-As-P material system
- High quality
- High reliability

Benefits

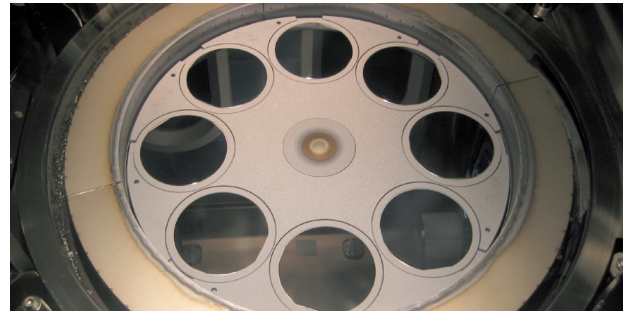
- Short development cycles and high flexibility
- Reduced development costs
- Short lead times
- Competitive prices

Epitaxial Services

2", 3", 4" and 6" wafers

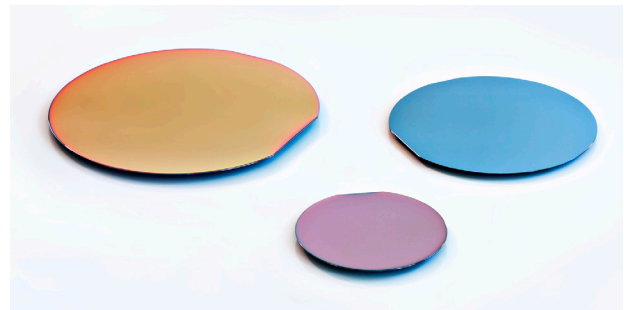
Profile

- Specialized on epitaxial wafers for high-quality and high-power applications
- Customer-specific structures
- Support from development projects to large scale production
- Customer-defined measurement schemes for epitaxial wafer characterization
- Extensive database of growth processes
- Our goal: A high yield in our customers' processes



Our Service

- High power laser diodes between 630 nm and 1200 nm
- Surface emitting lasers (VCSELs and VECSELs)
- RCLEDs
- LEDs and SLEDs
- Schottky Diodes
- Detectors



Our Expertise

- State-of-the-art growth equipment and processes
- Highly experienced staff
- Variety of materials and material combinations
- Extensive layer characterization: ECV, HRXRD, EL, PL, SEM, SIMS
- Tight control on starting materials and layer quality
- Certified according to ISO 9001:2008
- Protection of customer's intellectual property
- Stringent quality control

